

# Giuseppe Iannaccone

## List of Publications by Citations

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293  
papers

8,099  
citations

40  
h-index

82  
g-index

339  
ext. papers

9,608  
ext. citations

4  
avg, IF

6.28  
L-index

#	Paper	IF	Citations
293	Electronics based on two-dimensional materials. <i>Nature Nanotechnology</i> , <b>2014</b> , 9, 768-79	28.7	1953
292	Water-based and biocompatible 2D crystal inks for all-inkjet-printed heterostructures. <i>Nature Nanotechnology</i> , <b>2017</b> , 12, 343-350	28.7	335
291	Design criteria for the RF section of UHF and microwave passive RFID transponders. <i>IEEE Transactions on Microwave Theory and Techniques</i> , <b>2005</b> , 53, 2978-2990	4.1	267
290	Simulation of Graphene Nanoribbon Field-Effect Transistors. <i>IEEE Electron Device Letters</i> , <b>2007</b> , 28, 760-762	4.4	249
289	Performance of arsenene and antimonene double-gate MOSFETs from first principles. <i>Nature Communications</i> , <b>2016</b> , 7, 12585	17.4	224
288	Quantum engineering of transistors based on 2D materials heterostructures. <i>Nature Nanotechnology</i> , <b>2018</b> , 13, 183-191	28.7	198
287	. <i>IEEE Journal of Solid-State Circuits</i> , <b>2011</b> , 46, 465-474	5.5	164
286	. <i>IEEE Journal of Solid-State Circuits</i> , <b>2007</b> , 42, 1536-1542	5.5	161
285	Enhanced Shot Noise in Resonant Tunneling: Theory and Experiment. <i>Physical Review Letters</i> , <b>1998</b> , 80, 1054-1057	7.4	136
284	. <i>IEEE Sensors Journal</i> , <b>2016</b> , 16, 5452-5462	4	127
283	Lateral graphene-hBCN heterostructures as a platform for fully two-dimensional transistors. <i>ACS Nano</i> , <b>2012</b> , 6, 2642-8	16.7	115
282	Ultralow-Voltage Bilayer Graphene Tunnel FET. <i>IEEE Electron Device Letters</i> , <b>2009</b> , 30, 1096-1098	4.4	114
281	Performance Comparison of Graphene Nanoribbon FETs With Schottky Contacts and Doped Reservoirs. <i>IEEE Transactions on Electron Devices</i> , <b>2008</b> , 55, 2314-2323	2.9	108
280	Multiscale Modeling for Graphene-Based Nanoscale Transistors. <i>Proceedings of the IEEE</i> , <b>2013</b> , 101, 1653-1659	10.6	106
279	Threshold Voltage Instability in p-GaN Gate AlGaIn/GaN HFETs. <i>IEEE Transactions on Electron Devices</i> , <b>2018</b> , 65, 2454-2460	2.9	90
278	. <i>IEEE Transactions on Smart Grid</i> , <b>2015</b> , 6, 468-476	10.7	87
277	Electrical properties of graphene-metal contacts. <i>Scientific Reports</i> , <b>2017</b> , 7, 5109	4.9	82

276	Gate-Tunable Atomically Thin Lateral MoS <sub>2</sub> Schottky Junction Patterned by Electron Beam. <i>Nano Letters</i> , <b>2016</b> , 16, 3788-94	11.5	82
275	A Three-Dimensional Simulation Study of the Performance of Carbon Nanotube Field-Effect Transistors With Doped Reservoirs and Realistic Geometry. <i>IEEE Transactions on Electron Devices</i> , <b>2006</b> , 53, 1782-1788	2.9	75
274	On the Possibility of Tunable-Gap Bilayer Graphene FET. <i>IEEE Electron Device Letters</i> , <b>2009</b> , 30, 261-264	4.4	74
273	Heterojunction hybrid devices from vapor phase grown MoS <sub>2</sub> . <i>Scientific Reports</i> , <b>2014</b> , 4, 5458	4.9	65
272	An energy case for hybrid datacenters. <i>Operating Systems Review (ACM)</i> , <b>2010</b> , 44, 76-80	0.8	65
271	Low-voltage 2D materials-based printed field-effect transistors for integrated digital and analog electronics on paper. <i>Nature Communications</i> , <b>2020</b> , 11, 3566	17.4	61
270	All-2D Material Inkjet-Printed Capacitors: Toward Fully Printed Integrated Circuits. <i>ACS Nano</i> , <b>2019</b> , 13, 54-60	16.7	60
269	Shot noise in resonant-tunneling structures. <i>Physical Review B</i> , <b>1997</b> , 55, 4539-4550	3.3	54
268	Velocity saturation in few-layer MoS <sub>2</sub> transistor. <i>Applied Physics Letters</i> , <b>2013</b> , 103, 233509	3.4	52
267	A Semianalytical Model of Bilayer-Graphene Field-Effect Transistor. <i>IEEE Transactions on Electron Devices</i> , <b>2009</b> , 56, 2979-2986	2.9	49
266	Very Large Current Modulation in Vertical Heterostructure Graphene/hBN Transistors. <i>IEEE Transactions on Electron Devices</i> , <b>2013</b> , 60, 268-273	2.9	48
265	Effects due to backscattering and pseudogap features in graphene nanoribbons with single vacancies. <i>Physical Review B</i> , <b>2010</b> , 81,	3.3	48
264	General relation between density of states and dwell times in mesoscopic systems. <i>Physical Review B</i> , <b>1995</b> , 51, 4727-4729	3.3	48
263	Strong mobility degradation in ideal graphene nanoribbons due to phonon scattering. <i>Applied Physics Letters</i> , <b>2011</b> , 98, 212111	3.4	45
262	Physics-based compact model of nanoscale MOSFETs-Part I: transition from drift-diffusion to ballistic transport. <i>IEEE Transactions on Electron Devices</i> , <b>2005</b> , 52, 1795-1801	2.9	45
261	Three-dimensional simulation of nanocrystal Flash memories. <i>Applied Physics Letters</i> , <b>2001</b> , 78, 2046-2048	3.4	44
260	Modeling and manufacturability assessment of bistable quantum-dot cells. <i>Journal of Applied Physics</i> , <b>1999</b> , 85, 2962-2971	2.5	44
259	CMOS Silicon Physical Unclonable Functions Based on Intrinsic Process Variability. <i>IEEE Journal of Solid-State Circuits</i> , <b>2011</b> , 46, 1456-1463	5.5	43

258	Simulation of hydrogenated graphene field-effect transistors through a multiscale approach. <i>Physical Review B</i> , <b>2010</b> , 82,	3.3	43
257	Electric field control of spin rotation in bilayer graphene. <i>Nano Letters</i> , <b>2010</b> , 10, 4463-9	11.5	42
256	Design of a 75-nW, 0.5-V subthreshold complementary metal-oxide-semiconductor operational amplifier. <i>International Journal of Circuit Theory and Applications</i> , <b>2014</b> , 42, 967-977	2	41
255	An Open-Source Multiscale Framework for the Simulation of Nanoscale Devices. <i>IEEE Transactions on Electron Devices</i> , <b>2014</b> , 61, 48-53	2.9	40
254	Three-Dimensional Simulation of One-Dimensional Transport in Silicon Nanowire Transistors. <i>IEEE Nanotechnology Magazine</i> , <b>2007</b> , 6, 524-529	2.6	40
253	A Sub- $kT/q$ Voltage Reference Operating at 150 mV. <i>IEEE Transactions on Very Large Scale Integration (VLSI) Systems</i> , <b>2015</b> , 23, 1547-1551	2.6	39
252	An Ultralow-Voltage Energy-Efficient Level Shifter. <i>IEEE Transactions on Circuits and Systems II: Express Briefs</i> , <b>2017</b> , 64, 61-65	3.5	38
251	Two-dimensional hole precession in an all-semiconductor spin field effect transistor. <i>Physical Review B</i> , <b>2004</b> , 69,	3.3	38
250	Modeling of Tunnelling Currents in Hf-Based Gate Stacks as a Function of Temperature and Extraction of Material Parameters. <i>IEEE Transactions on Electron Devices</i> , <b>2007</b> , 54, 83-89	2.9	36
249	Growth-Induced Strain in Chemical Vapor Deposited Monolayer MoS <sub>2</sub> : Experimental and Theoretical Investigation. <i>Advanced Materials Interfaces</i> , <b>2017</b> , 4, 1700031	4.6	35
248	. <i>IEEE Transactions on Electron Devices</i> , <b>2011</b> , 58, 2824-2830	2.9	34
247	Physics-based compact model of nanoscale MOSFETs-Part II: effects of degeneracy on transport. <i>IEEE Transactions on Electron Devices</i> , <b>2005</b> , 52, 1802-1806	2.9	34
246	GaN Nanowire n-MOSFET With 5 nm Channel Length for Applications in Digital Electronics. <i>IEEE Electron Device Letters</i> , <b>2017</b> , 38, 859-862	4.4	33
245	Bilayer Graphene Transistors for Analog Electronics. <i>IEEE Transactions on Electron Devices</i> , <b>2014</b> , 61, 729-733	3.3	31
244	Analogue two-dimensional semiconductor electronics. <i>Nature Electronics</i> , <b>2020</b> , 3, 486-491	28.4	31
243	Coupled Mode Space Approach for the Simulation of Realistic Carbon Nanotube Field-Effect Transistors. <i>IEEE Nanotechnology Magazine</i> , <b>2007</b> , 6, 475-480	2.6	29
242	Ultralow Specific Contact Resistivity in Metal-Graphene Junctions via Contact Engineering. <i>Advanced Materials Interfaces</i> , <b>2019</b> , 6, 1801285	4.6	29
241	High performance metal-insulator-graphene diodes for radio frequency power detection application. <i>Nanoscale</i> , <b>2017</b> , 9, 11944-11950	7.7	28

240	Modelling and simulation challenges for nanoscale MOSFETs in the ballistic limit. <i>Solid-State Electronics</i> , <b>2004</b> , 48, 581-587	1.7	26
239	A QCA cell in silicon-on-insulator technology: theory and experiment. <i>Superlattices and Microstructures</i> , <b>2003</b> , 34, 205-211	2.8	26
238	First-Principles Simulations of FETs Based on Two-Dimensional InSe. <i>IEEE Electron Device Letters</i> , <b>2018</b> , 39, 626-629	4.4	25
237	Vertical transport in graphene-hexagonal boron nitride heterostructure devices. <i>Scientific Reports</i> , <b>2015</b> , 5, 14519	4.9	25
236	Model of tunneling transistors based on graphene on SiC. <i>Applied Physics Letters</i> , <b>2010</b> , 96, 133508	3.4	25
235	Comparison of Modeling Approaches for the Capacitance-Voltage and Current-Voltage Characteristics of Advanced Gate Stacks. <i>IEEE Transactions on Electron Devices</i> , <b>2007</b> , 54, 106-114	2.9	25
234	Rashba spin precession in quantum-Hall edge channels. <i>Physical Review B</i> , <b>2005</b> , 71,	3.3	25
233	Simulation of a quantum-dot flash memory. <i>Journal of Applied Physics</i> , <b>1998</b> , 84, 5032-5036	2.5	25
232	Graphene-based lateral heterostructure transistors exhibit better intrinsic performance than graphene-based vertical transistors as post-CMOS devices. <i>Scientific Reports</i> , <b>2014</b> , 4, 6607	4.9	24
231	Junction Engineering of 1T-DRAMs. <i>IEEE Electron Device Letters</i> , <b>2013</b> , 34, 408-410	4.4	24
230	Transistor Concepts Based on Lateral Heterostructures of Metallic and Semiconducting Phases of MoS <sub>2</sub> . <i>Physical Review Applied</i> , <b>2017</b> , 8,	4.3	24
229	On the role of interface states in low-voltage leakage currents of metal-oxide-semiconductor structures. <i>Applied Physics Letters</i> , <b>2002</b> , 80, 4597-4599	3.4	24
228	. <i>IEEE Nanotechnology Magazine</i> , <b>2015</b> , 14, 1068-1082	2.6	23
227	Two-Dimensional Tunnel Transistors Based on $\text{Bi}_2\text{Se}_3$ Thin Film. <i>IEEE Electron Device Letters</i> , <b>2014</b> , 35, 129-131	4.4	23
226	Enhancement and suppression of shot noise in capacitively coupled metallic double dots. <i>Physical Review B</i> , <b>2002</b> , 65,	3.3	22
225	Lateral Heterostructure Field-Effect Transistors Based on Two-Dimensional Material Stacks with Varying Thickness and Energy Filtering Source. <i>ACS Nano</i> , <b>2020</b> , 14, 1982-1989	16.7	21
224	Reconfigurable Diodes Based on Vertical WSe Transistors with van der Waals Bonded Contacts. <i>Advanced Materials</i> , <b>2018</b> , 30, e1707200	24	21
223	Analytical model for the 1/f noise in the tunneling current through metal-oxide-semiconductor structures. <i>Journal of Applied Physics</i> , <b>2009</b> , 106, 073710	2.5	21

222	Analytical Model of One-Dimensional Carbon-Based Schottky-Barrier Transistors. <i>IEEE Transactions on Electron Devices</i> , <b>2010</b> , 57, 1616-1625	2.9	21
221	Theory and experiment of suppressed shot noise in 'stress-induced leakage currents. <i>IEEE Transactions on Electron Devices</i> , <b>2003</b> , 50, 1363-1369	2.9	21
220	Flexible One-Dimensional MetalInsulatorGraphene Diode. <i>ACS Applied Electronic Materials</i> , <b>2019</b> , 1, 945-950	4	20
219	Perspectives of graphene nanoelectronics: probing technological options with modeling <b>2009</b> ,		20
218	CMOS unclonable system for secure authentication based on device variability <b>2008</b> ,		20
217	Effect of dephasing on the current statistics of mesoscopic devices. <i>Physical Review Letters</i> , <b>2004</b> , 93, 256803	7.4	20
216	Statistical model of dephasing in mesoscopic devices introduced in the scattering matrix formalism. <i>Physical Review B</i> , <b>2004</b> , 69,	3.3	20
215	Semiclassical simulation of quantum cellular automaton circuits. <i>International Journal of Circuit Theory and Applications</i> , <b>2001</b> , 29, 37-47	2	20
214	Thermal behavior of quantum cellular automaton wires. <i>Journal of Applied Physics</i> , <b>2000</b> , 87, 7320-7325	2.5	20
213	. <i>IEEE Transactions on Electron Devices</i> , <b>2010</b> , 57, 1936-1941	2.9	19
212	. <i>IEEE Nanotechnology Magazine</i> , <b>2005</b> , 4, 360-368	2.6	19
211	Compact formula for the density of states in a quantum well. <i>Physical Review B</i> , <b>1996</b> , 53, 2020-2025	3.3	19
210	High-Performance 2D p-Type Transistors Based on GaSe Layers: An Ab Initio Study. <i>Advanced Electronic Materials</i> , <b>2017</b> , 3, 1600399	6.4	18
209	<b>2013</b> ,		18
208	Suppressed shot noise in trap-assisted tunneling of metaloxideSemiconductor capacitors. <i>Applied Physics Letters</i> , <b>2000</b> , 77, 2876-2878	3.4	18
207	Characteristic times in the motion of a particle. <i>Physical Review B</i> , <b>1994</b> , 49, 16548-16560	3.3	18
206	Effective Bohm Quantum Potential for device simulators based on drift-diffusion and energy transport <b>2004</b> , 275-278		18
205	The Role of Silicon Substrate on the Leakage Current Through GaN-on-Si Epitaxial Layers. <i>IEEE Transactions on Electron Devices</i> , <b>2018</b> , 65, 51-58	2.9	17

204	Shot Noise Suppression in Quasi-One-Dimensional Field-Effect Transistors. <i>IEEE Transactions on Electron Devices</i> , <b>2009</b> , 56, 2137-2143	2.9	17
203	Analysis of shot noise suppression in mesoscopic cavities in a magnetic field. <i>Europhysics Letters</i> , <b>2006</b> , 73, 574-580	1.6	17
202	Detailed modeling of sub-100-nm MOSFETs based on Schrödinger DD per subband and experiments and evaluation of the performance gap to ballistic transport. <i>IEEE Transactions on Electron Devices</i> , <b>2005</b> , 52, 1851-1858	2.9	17
201	Performance assessment of adiabatic quantum cellular automata. <i>Journal of Applied Physics</i> , <b>2001</b> , 89, 6435-6443	2.5	17
200	Modeling of Electron Devices Based on 2-D Materials. <i>IEEE Transactions on Electron Devices</i> , <b>2018</b> , 65, 4167-4179	2.9	16
199	First principles investigation of tunnel FETs based on nanoribbons from topological two-dimensional materials. <i>Nanoscale</i> , <b>2017</b> , 9, 19390-19397	7.7	16
198	Geometrical Effects on Valley-Orbital Filling Patterns in Silicon Quantum Dots for Robust Qubit Implementation. <i>Applied Physics Express</i> , <b>2012</b> , 5, 124001	2.4	16
197	Direct Solution of the Boltzmann Transport Equation and Poisson-Schrödinger Equation for Nanoscale MOSFETs. <i>IEEE Transactions on Electron Devices</i> , <b>2007</b> , 54, 2901-2909	2.9	16
196	Analytical and Numerical Investigation of Noise in Nanoscale Ballistic Field Effect Transistors. <i>Journal of Computational Electronics</i> , <b>2004</b> , 3, 199-202	1.8	16
195	Modeling of ballistic nanoscale metal-oxide-semiconductor field effect transistors. <i>Applied Physics Letters</i> , <b>2002</b> , 81, 3672-3674	3.4	16
194	A Steep-Slope MoS <sub>2</sub> -Nanoribbon MOSFET Based on an Intrinsic Cold-Contact Effect. <i>IEEE Electron Device Letters</i> , <b>2019</b> , 40, 1550-1553	4.4	15
193	Insights on radio frequency bilayer graphene FETs <b>2012</b> ,		15
192	Low-Voltage Low-Power CMOS Oscillator with Low Temperature and Process Sensitivity <b>2007</b> ,		15
191	Ultra low power RF section of a passive microwave RFID transponder in 0.35 $\mu\text{m}$ BiCMOS		15
190	Modelling and simulation of charging and discharging processes in nanocrystal flash memories during program and erase operations. <i>Solid-State Electronics</i> , <b>2005</b> , 49, 1745-1753	1.7	15
189	Status and perspectives of nanoscale device modelling. <i>Nanotechnology</i> , <b>2001</b> , 12, 136-142	3.4	15
188	Simulation of time evolution of clocked and nonclocked quantum cellular automaton circuits. <i>Journal of Applied Physics</i> , <b>2002</b> , 92, 3169-3178	2.5	15
187	Four-phase power clock generator for adiabatic logic circuits. <i>Electronics Letters</i> , <b>2002</b> , 38, 689	1.1	15

186	Modelling of self-organized InAs quantum dots embedded in an AlGaAs/GaAs heterostructure. <i>Nanotechnology</i> , <b>2002</b> , 13, 263-266	3.4	15
185	A picopower temperature-compensated, subthreshold CMOS voltage reference. <i>International Journal of Circuit Theory and Applications</i> , <b>2014</b> , 42, 1306-1318	2	14
184	A comparison of advanced transport models for the computation of the drain current in nanoscale nMOSFETs. <i>Solid-State Electronics</i> , <b>2009</b> , 53, 1293-1302	1.7	14
183	Barrier Lowering and Backscattering Extraction in Short-Channel MOSFETs. <i>IEEE Transactions on Electron Devices</i> , <b>2010</b> , 57, 2132-2137	2.9	14
182	A 109 nW, 44 ppm/°C CMOS Current Reference with Low Sensitivity to Process Variations <b>2007</b> ,		14
181	Operation of quantum cellular automaton cells with more than two electrons. <i>Applied Physics Letters</i> , <b>1999</b> , 75, 3198-3200	3.4	14
180	Material-Device-Circuit Co-optimization of 2D Material based FETs for Ultra-Scaled Technology Nodes. <i>Scientific Reports</i> , <b>2017</b> , 7, 5016	4.9	13
179	Advantages of the FinFET architecture in SONOS and Nanocrystal memory devices <b>2007</b> ,		13
178	Unified approach to electron transport in double-barrier structures. <i>Physical Review B</i> , <b>1995</b> , 52, 17406-17412	3.4	13
177	Comparison of short-channel effects in monolayer MoS <sub>2</sub> based junctionless and inversion-mode field-effect transistors. <i>Applied Physics Letters</i> , <b>2016</b> , 108, 023506	3.4	13
176	Simulation of the Performance of Graphene FETs With a Semiclassical Model, Including Band-to-Band Tunneling. <i>IEEE Transactions on Electron Devices</i> , <b>2014</b> , 61, 1567-1574	2.9	12
175	The fast tracker processor for hadron collider triggers. <i>IEEE Transactions on Nuclear Science</i> , <b>2001</b> , 48, 575-580	1.7	12
174	Quantum analysis of shot noise suppression in a series of tunnel barriers. <i>Physical Review B</i> , <b>2009</b> , 79,	3.3	11
173	Drift velocity peak and negative differential mobility in high field transport in graphene nanoribbons explained by numerical simulations. <i>Applied Physics Letters</i> , <b>2011</b> , 99, 242108	3.4	11
172	Ultra-low-power series voltage regulator for passive RFID transponders with subthreshold logic. <i>Electronics Letters</i> , <b>2006</b> , 42, 1350	1.1	11
171	Ultra-low-power temperature compensated voltage reference generator. <i>Microelectronics Journal</i> , <b>2006</b> , 37, 1072-1079	1.8	11
170	Hadron collider triggers with high-quality tracking at very high event rates. <i>IEEE Transactions on Nuclear Science</i> , <b>2004</b> , 51, 391-400	1.7	11
169	Dependence of the programming window of silicon-on-insulator nanocrystal memories on channel width. <i>Applied Physics Letters</i> , <b>2005</b> , 86, 113502	3.4	11



168	Proposed experiment to assess operation of quantum cellular automaton cells. <i>Journal of Applied Physics</i> , <b>2001</b> , 90, 6428-6433	2.5	11
167	A three-dimensional solver of the Schrödinger equation in momentum space for the detailed simulation of nanostructures. <i>Nanotechnology</i> , <b>2002</b> , 13, 369-372	3.4	11
166	The effect of quantum confinement and discrete dopants in nanoscale 50 nm n-MOSFETs: a three-dimensional simulation. <i>Nanotechnology</i> , <b>2002</b> , 13, 294-298	3.4	11
165	Noise measurements in resonant tunnelling structures as a function of current and temperature. <i>Electronics Letters</i> , <b>1995</b> , 31, 503-505	1.1	11
164	Insights on the physics and application of off-plane quantum transport through graphene and 2D materials. <i>Solid-State Electronics</i> , <b>2016</b> , 115, 213-218	1.7	10
163	On Transport in Vertical Graphene Heterostructures. <i>IEEE Electron Device Letters</i> , <b>2014</b> , 35, 966-968	4.4	10
162	NANOTCAD2D: Two-dimensional code for the simulation of nanoelectronic devices and structures. <i>Computational Materials Science</i> , <b>2003</b> , 28, 342-352	3.2	10
161	Characterization of soft breakdown in thin oxide NMOSFETs based on the analysis of the substrate current. <i>IEEE Transactions on Electron Devices</i> , <b>2001</b> , 48, 1109-1113	2.9	10
160	. <i>IEEE Access</i> , <b>2020</b> , 8, 203525-203537	3.5	10
159	Atomistic quantum transport modeling of metal-graphene nanoribbon heterojunctions. <i>Physical Review B</i> , <b>2010</b> , 82,	3.3	9
158	Statistical theory of shot noise in quasi-one-dimensional field-effect transistors in the presence of electron-electron interaction. <i>Physical Review B</i> , <b>2010</b> , 81,	3.3	9
157	Performance Analysis of Graphene Bilayer Transistors Through Tight-Binding Simulations <b>2009</b> ,		9
156	A model for MOS gate stack quality evaluation based on the gate current 1/f noise <b>2008</b> ,		9
155	A 300 nW, 12 ppm//spl deg/C Voltage Reference in a Digital 0.35 /spl mu/m CMOS Process		9
154	Numerical investigation of shot-noise suppression in diffusive conductors. <i>Physical Review B</i> , <b>2003</b> , 67,	3.3	9
153	Code for the 3D Simulation of Nanoscale Semiconductor Devices, Including Drift-Diffusion and Ballistic Transport in 1D and 2D Subbands, and 3D Tunneling. <i>Journal of Computational Electronics</i> , <b>2005</b> , 4, 63-66	1.8	9
152	Performance of carbon nanotube field effect transistors with doped source and drain extensions and arbitrary geometry		9
151	Extraction of parameters of surface states from experimental test structures. <i>Nanotechnology</i> , <b>2002</b> , 13, 373-377	3.4	9

150	On the approach to the stationary-state-scattering limit within Bohmian mechanics. <i>Physics Letters, Section A: General, Atomic and Solid State Physics</i> , <b>1995</b> , 208, 17-24	2.3	9
149	Stacking and interlayer electron transport in MoS <sub>2</sub> . <i>Physical Review B</i> , <b>2018</b> , 98,	3.3	9
148	Characterization and modeling of CMOS-compatible acoustical particle velocity sensors for applications requiring low supply voltages. <i>Sensors and Actuators A: Physical</i> , <b>2015</b> , 229, 192-202	3.9	8
147	Inkjet-printed graphene Hall mobility measurements and low-frequency noise characterization. <i>Nanoscale</i> , <b>2020</b> , 12, 6708-6716	7.7	8
146	Quantum transport modeling of defected graphene nanoribbons. <i>Physica E: Low-Dimensional Systems and Nanostructures</i> , <b>2012</b> , 44, 981-984	3	8
145	. <i>IEEE Transactions on Electron Devices</i> , <b>2011</b> , 58, 691-697	2.9	8
144	Shot noise partial suppression in the SILO regime. <i>Microelectronics Reliability</i> , <b>2000</b> , 40, 1605-1608	1.2	8
143	A portable class of 3-transistor current references with low-power sub-0.5 V operation. <i>International Journal of Circuit Theory and Applications</i> , <b>2018</b> , 46, 779-795	2	7
142	Compact drain-current model for reproducing advanced transport models in nanoscale double-gate MOSFETs. <i>Semiconductor Science and Technology</i> , <b>2011</b> , 26, 095015	1.8	7
141	Probing Pauli blocking with shot noise in resonant tunneling diodes: Experiment and theory. <i>Physical Review B</i> , <b>2007</b> , 75,	3.3	7
140	Three-dimensional Simulation of the dependence of the programming window of SOI nanocrystal memories on the channel width. <i>IEEE Nanotechnology Magazine</i> , <b>2005</b> , 4, 326-330	2.6	7
139	Channel noise modelling of nanoMOSFETs in a partially ballistic transport regime. <i>Journal of Computational Electronics</i> , <b>2006</b> , 5, 91-95	1.8	7
138	Internet-of-things infrastructure as a platform for distributed measurement applications <b>2015</b> ,		6
137	A 220-mV input, 8.6 step-up voltage conversion ratio, 10.45-W output power, fully integrated switched-capacitor converter for energy harvesting <b>2017</b> ,		6
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133	An ultra-low-power, temperature compensated voltage reference generator		6

132	Quantum confinement in silicon-germanium electron waveguides. <i>Nanotechnology</i> , <b>2002</b> , 13, 267-273	3.4	6
131	Coulomb breach effect emerging in shot noise. <i>Nanotechnology</i> , <b>1999</b> , 10, 97-101	3.4	6
130	Tunnel-Field-Effect Spin Filter from Two-Dimensional Antiferromagnetic Stanene. <i>Physical Review Applied</i> , <b>2018</b> , 10,	4.3	6
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123	Study of Warm-Electron Injection in Double-Gate SONOS by Full-Band Monte Carlo Simulation. <i>IEEE Electron Device Letters</i> , <b>2008</b> , 29, 1242-1244	4.4	5
122	Performance Comparison of Graphene Nanoribbon Schottky Barrier and MOS FETs <b>2007</b> ,		5
121	Three-dimensional atomistic simulation of carbon nanotube FETs with realistic geometry		5
120	Analytical model for nanowire and nanotube transistors covering both dissipative and ballistic transport		5
119	Three-dimensional simulation of realistic single electron transistors. <i>IEEE Nanotechnology Magazine</i> , <b>2005</b> , 4, 415-421	2.6	5
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117	Low frequency current noise in unstressed/stressed thin oxide metal-oxide-semiconductor capacitors. <i>Solid-State Electronics</i> , <b>2002</b> , 46, 1807-1813	1.7	5
116	Adiabatic 4-bit adders: comparison of performance and robustness against technology parameter variations		5
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113	Monte Carlo simulation of electromigration in polycrystalline metal stripes. <i>Semiconductor Science and Technology</i> , <b>2000</b> , 15, 608-612	1.8	5
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100	Analytical drain current model reproducing advanced transport models in nanoscale cylindrical surrounding-gate (SRG) MOSFETs. <i>Journal of Applied Physics</i> , <b>2011</b> , 110, 034510	2.5	4
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63	Nanodevices in Flatland: Two-dimensional graphene-based transistors with high Ion/Ioff ratio <b>2011</b> ,		2
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44	A software platform for nanoscale device simulation and visualization <b>2009,</b>		1
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40	3D simulation of a silicon quantum dot in a magnetic field based on current spin density functional theory. <i>Journal of Computational Electronics</i> , <b>2007</b> , 6, 191-194	1.8	1
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35	Three-dimensional simulation of single electron transistors		1
34	Evaluation of performance and perspectives of nanocrystal flash memories based on 3D quantum modeling		1
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